

# Phase Control Thyristors (Hockey PUK Version), 960 A



E-PUK (TO-200AB)

PRIMARY CHARACTERISTICS					
I <sub>T(AV)</sub>	960 A				
$V_{DRM}/V_{RRM}$	400 V, 600 V				
$V_{TM}$	1.60 V				
I <sub>GT</sub>	100 mA				
T <sub>J</sub>	-40 °C to +125 °C				
Package	E-PUK (TO-200AB)				
Circuit configuration	Single SCR				

#### **FEATURES**

- · Center amplifying gate
- Metal case with ceramic insulator
- International standard case E-PUK (TO-200AB)



- Low profile hockey PUK to increase current-carrying capability
- · Designed and qualified for industrial level
- Material categorization: for definitions of compliance please see <a href="https://www.vishay.com/doc?99912">www.vishay.com/doc?99912</a>

#### **TYPICAL APPLICATIONS**

- · DC motor controls
- Controlled DC power supplies
- AC controllers

MAJOR RATINGS AND CHARACTERISTICS						
PARAMETER	TEST CONDITIONS	VALUES	UNITS			
		960	А			
I <sub>T(AV)</sub>	T <sub>hs</sub>	55	°C			
1		1900	Α			
I <sub>T(RMS)</sub>	T <sub>hs</sub>	25	°C			
1	50 Hz	15 000	٨			
ITSM	60 Hz	15 700	Α			
l <sup>2</sup> t	50 Hz	1130	kA <sup>2</sup> s			
1 <del>-</del> 1	60 Hz	1030	KA-S			
V <sub>DRM</sub> /V <sub>RRM</sub>		400 to 600	V			
tq	Typical	100	μs			
T <sub>J</sub>		-40 to 125	°C			

#### **ELECTRICAL SPECIFICATIONS**

VOLTAGE RATINGS								
TYPE NUMBER	VOLTAGE CODE	V <sub>DRM</sub> /V <sub>RRM</sub> , MAXIMUM REPETITIVE PEAK AND OFF-STATE VOLTAGE V	V <sub>RSM</sub> , MAXIMUM NON-REPETITIVE PEAK VOLTAGE V	$\begin{aligned} I_{DRM}/I_{RRM}MAXIMUM\\ ATT_J = T_J\\ MAXIMUMmA \end{aligned}$				
VS-ST380CC	04	400	500	50				
VS-51360CC 06		600	700	30				



ABSOLUTE MAXIMUM RATINGS	3					
PARAMETER	SYMBOL		TEST CONDITIONS			
Maximum average on-state current	1	180° condu	180° conduction, half sine wave			Α
at heatsink temperature	I <sub>T(AV)</sub>	double side	(single side) co	oled	55 (75)	°C
Maximum RMS on-state current	I <sub>T(RMS)</sub>	DC at 25 °C	heatsink tempe	erature double side cooled	1900	
		t = 10 ms	No voltage		15 000	
Maximum peak, one-cycle		t = 8.3 ms	reapplied		15 700	A kA <sup>2</sup> s
non-repetitive surge current	I <sub>TSM</sub>	t = 10 ms	100 % V <sub>RRM</sub>		12 600	
		t = 8.3 ms	reapplied	Sinusoidal half wave,	13 200	
Maximum I <sup>2</sup> t for fusing	l <sup>2</sup> t	t = 10 ms	No voltage reapplied	initial $T_J = T_J$ maximum	1130	
		t = 8.3 ms			1030	
		t = 10 ms			800	
	t = 8.3 ms reapplied			725		
Maximum I <sup>2</sup> √t for fusing	I²√t	t = 0.1 to 10	t = 0.1 to 10 ms, no voltage reapplied			kA²√s
Low level value of threshold voltage	V <sub>T(TO)1</sub>	(16.7 % x π	(16.7 % x $\pi$ x $I_{T(AV)}$ < I < $\pi$ x $I_{T(AV)}$ ), $T_J = T_J$ maximum			V
High level value of threshold voltage	V <sub>T(TO)2</sub>	$(I > \pi \times I_{T(AV)})$	$(I > \pi \times I_{T(AV)}), T_J = T_J \text{ maximum}$			\ \ \
Low level value of on-state slope resistance	r <sub>t1</sub>	(16.7 % x π	(16.7 % x $\pi$ x $I_{T(AV)}$ < I < $\pi$ x $I_{T(AV)}$ ), $T_J = T_J$ maximum			mΩ
High level value of on-state slope resistance	r <sub>t2</sub>	$(I > \pi \times I_{T(AV)})$ , $T_J = T_J$ maximum			0.24	11152
Maximum on-state voltage	$V_{TM}$	$I_{pk} = 3000 \text{ A}, T_J = T_J \text{ maximum}, t_p = 10 \text{ ms sine pulse}$			1.60	V
Maximum holding current	I <sub>H</sub>	T _ 05 °C	anada aunnis 1	2 V registive lead	600	mA
Typical latching current	ΙL	T <sub>J</sub> = 25 °C, anode supply 12 V resistive load			1000	IIIA

SWITCHING				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum non-repetitive rate of rise of turned-on current	dl/dt	Gate drive 20 V, 20 $\Omega$ , $t_r \le 1~\mu s$ $T_J = T_J$ maximum, anode voltage $\le 80~\%~V_{DRM}$	1000	A/μs
Typical delay time	t <sub>d</sub>	Gate current 1 A, $dl_g/dt = 1 A/\mu s$ $V_d = 0.67 \% V_{DRM}, T_J = 25 °C$	1.0	
Typical turn-off time	t <sub>q</sub>	$\begin{array}{c} I_{TM}=550~A,~T_J=T_J~maximum,~dl/dt=40~A/\mu s,\\ V_R=50~V,~dV/dt=20~V/\mu s,~gate~0~V~100~\Omega,~t_p=500~\mu s \end{array}$	100	μs

BLOCKING				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum critical rate of rise of off-state voltage	dV/dt	$T_J = T_J$ maximum linear to 80 % rated $V_{DRM}$	500	V/µs
Maximum peak reverse and off-state leakage current	I <sub>RRM,</sub> I <sub>DRM</sub>	$T_J = T_J$ maximum, rated $V_{DRM}/V_{RRM}$ applied	50	mA



TRIGGERING						
PARAMETER	ARAMETER SYMBOL TEST CONDITIONS		VALUES		UNITS	
PARAMETER	STINIBUL	IES	SI CONDITIONS	TYP.	MAX.	UNITS
Maximum peak gate power	$P_{GM}$	$T_J = T_J$ maximum,	t <sub>p</sub> ≤ 5 ms	10.0		w
Maximum average gate power	P <sub>G(AV)</sub>	$T_J = T_J$ maximum,	f = 50 Hz, d% = 50	2	.0	VV
Maximum peak positive gate current	I <sub>GM</sub>	$T_J = T_J$ maximum,	t <sub>p</sub> ≤ 5 ms	3	.0	Α
Maximum peak positive gate voltage	+ V <sub>GM</sub>	T T manyimum i	t < E ma	20		V
Maximum peak negative gate voltage	- V <sub>GM</sub>	$T_J = T_J$ maximum, $t_p \le 5$ ms			5.0	
	I <sub>GT</sub>	T <sub>J</sub> = -40 °C	Maximum required gate trigger/	200	-	
DC gate current required to trigger		T <sub>J</sub> = 25 °C		100	200	mA
		T <sub>J</sub> = 125 °C	current/voltage are the lowest		-	
		T <sub>J</sub> = -40 °C	value which will trigger all units	2.5	-	
DC gate voltage required to trigger	$V_{GT}$	T <sub>J</sub> = 25 °C	12 V anode to cathode applied	1.8	3.0	٧
		T <sub>J</sub> = 125 °C		1.1	-	
DC gate current not to trigger	I <sub>GD</sub>	T T manyimay	Maximum gate current/voltage not to trigger is the maximum	10		mA
DC gate voltage not to trigger	$V_{GD}$	$T_J = T_J$ maximum value which will not trigger any unit with rated $V_{DRM}$ anode to cathode applied		0.	25	V

THERMAL AND MECHANICAL SPECIFICATIONS					
PARAMETER	SYMBOL	BOL TEST CONDITIONS		UNITS	
Maximum operating junction temperature range	$T_{J}$		-40 to 125	°C	
Maximum storage temperature range	T <sub>Stg</sub>		-40 to 150		
Maximum thermal resistance, junction to heatsink	D	DC operation single side cooled	0.09		
	R <sub>thJ-hs</sub>	DC operation double side cooled	0.04	K/W	
Maximum thermal resistance, case to heatsink	R <sub>thC-hs</sub>	DC operation single side cooled 0.		IV/VV	
Maximum thermal resistance, case to heatslink		DC operation double side cooled	0.01		
Mounting force, ± 10 %			9800 (1000)	N (kg)	
Approximate weight			83	g	
Case style		See dimensions - link at the end of datasheet	E-PUK (TO-2	200AB)	

△R <sub>thJ-hs</sub> CONDUCTION							
CONDUCTION ANGLE	SINUSOIDAL CONDUCTION		RECTANGULAR CONDUCTION		TEGT COMPITIONS	UNITS	
CONDUCTION ANGLE	SINGLE SIDE	DOUBLE SIDE	SINGLE SIDE	DOUBLE SIDE	TEST CONDITIONS	UNITS	
180°	0.010	0.011	0.007	0.007	T <sub>J</sub> = T <sub>J</sub> maximum		
120°	0.012	0.012	0.012	0.013			
90°	0.015	0.015	0.016	0.017		K/W	
60°	0.022	0.022	0.023	0.023			
30°	0.036	0.036	0.036	0.037			

#### Note

• The table above shows the increment of thermal resistance R<sub>thJ-hs</sub> when devices operate at different conduction angles than DC



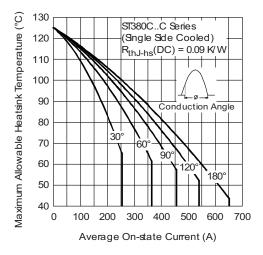


Fig. 1 - Current Ratings Characteristics

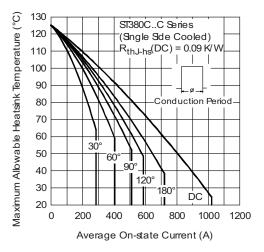


Fig. 2 - Current Ratings Characteristics

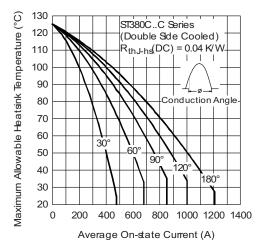


Fig. 3 - Current Ratings Characteristics

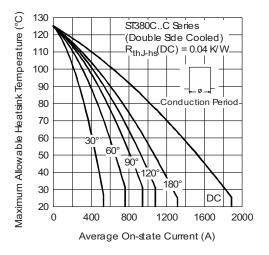


Fig. 4 - Current Ratings Characteristics

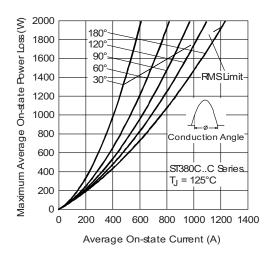


Fig. 5 - On-State Power Loss Characteristics

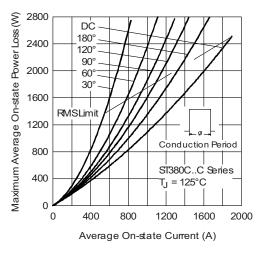


Fig. 6 - On-State Power Loss Characteristics

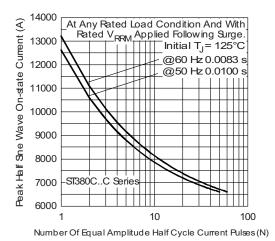


Fig. 7 - Maximum Non-Repetitive Surge Current Single and Double Side Cooled

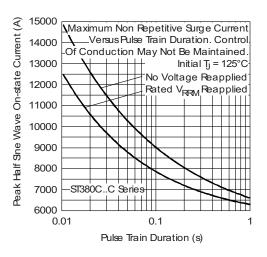


Fig. 8 - Maximum Non-Repetitive Surge Current Single and Double Side Cooled

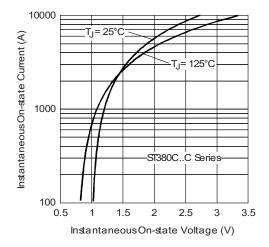


Fig. 9 - On-State Voltage Drop Characteristics

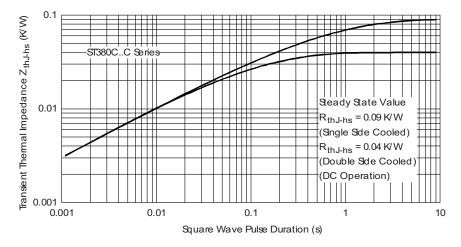


Fig. 10 - Thermal Impedance  $Z_{thJ\text{-}hs}$  Characteristics

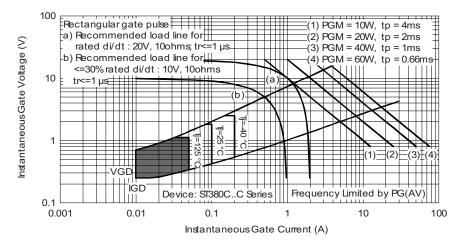
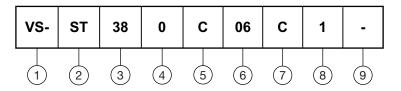


Fig. 11 - Gate Characteristics

#### **ORDERING INFORMATION TABLE**

**Device code** 



1 - Vishay Semiconductors product

|2| - Thyristor

3 - Essential part number

4 - 0 = converter grade

5 - C = ceramic PUK

6 - Voltage code x 100 = V<sub>RRM</sub> (see Voltage Ratings table)

7 - C = PUK case E-PUK (TO-200AB)

- 0 = eyelet terminals (gate and auxiliary cathode unsoldered leads)

1 = fast-on terminals (gate and auxiliary cathode unsoldered leads)

2 = eyelet terminals (gate and auxiliary cathode soldered leads)

3 = fast-on terminals (gate and auxiliary cathode soldered leads)

9 - Critical dV/dt: • None = 500 V/µs (standard selection)

• L = 1000 V/µs (special selection)

LINKS TO RELATED DOCUMENTS				
Dimensions	http://www.vishay.com/doc?95075			

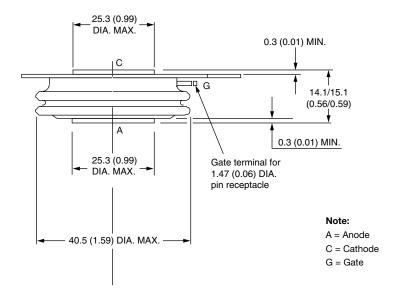


# E-PUK (TO-200AB)

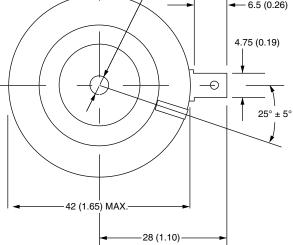
#### **DIMENSIONS** in millimeters (inches)

Anode to gate

Creepage distance: 11.18 (0.44) minimum Strike distance: 7.62 (0.30) minimum



2 holes 3.56 (0.14) x 1.83 (0.07) minimum deep



Quote between upper and lower pole pieces has to be considered after application of mounting force (see thermal and mechanical specification)



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